

GA10JT12-263 Information


For Reference Only

Part Number [GA10JT12-263](#)
Manufacturer GeneSiC Semiconductor
Category Discrete Semiconductor Products
[Transistors - FETs, MOSFETs - Single](#)
Description TRANS SJT 1200V 25A
Package -
 For the pricing/inventory/lead time, please contact us
 Website: <https://www.heisener.com>
 E-mail: salesdept@heisener.com


[Request a Quote](#)
Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.


GA10JT12-263 Specifications

Manufacturer Part Number	GA10JT12-263
Manufacturer	GeneSiC Semiconductor
Category	Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single
Package	-
Series	-
FET Type	-
Technology	SiC (Silicon Carbide Junction Transistor)
Drain to Source Voltage (Vdss)	1200V
Current - Continuous Drain (Id) @ 25°C	25A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	-
Vgs(th) (Max) @ Id	-
Gate Charge (Qg) (Max) @ Vgs	-
Input Capacitance (Ciss) (Max) @ Vds	1403pF @ 800V
Vgs (Max)	-
FET Feature	-
Power Dissipation (Max)	170W (Tc)
Rds On (Max) @ Id, Vgs	120 mOhm @ 10A
Operating Temperature	175°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	-
Package / Case	-

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GA10JT12-263 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GA10JT12-263 Payment Methods



GA10JT12-263 Shipping Methods



If you have any question about GA10JT12-263, please do not hesitate to contact us!

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